## 1. General description

NPN/PNP general-purpose transistor in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Low package height of 0.37 mm

## 3. Applications

- General-purpose switching and amplification
- Mobile applications

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	45	V
I <sub>C</sub>	collector current			-	-	100	mA
Per transistor; for the PNP transistor with negative polarity							
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C		200	-	450	



# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	
3	C2	collector TR2	2 5	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	3 4	E1 B1 C2
6	C1	collector TR1	Transparent top view	sym139
7	C1	collector TR1	DFN1010B-6 (SOT1216)	
8	C2	collector TR2		

# 6. Ordering information

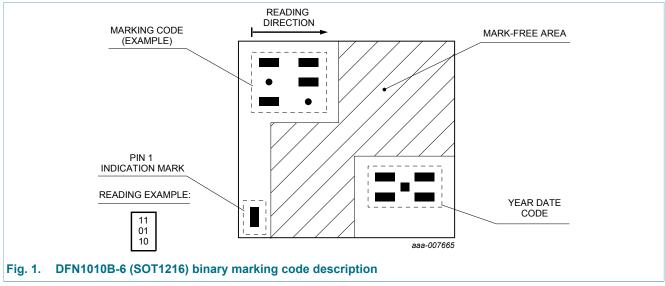
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BC847QAPN	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BC847QAPN	01 00 00



BC847QAPN

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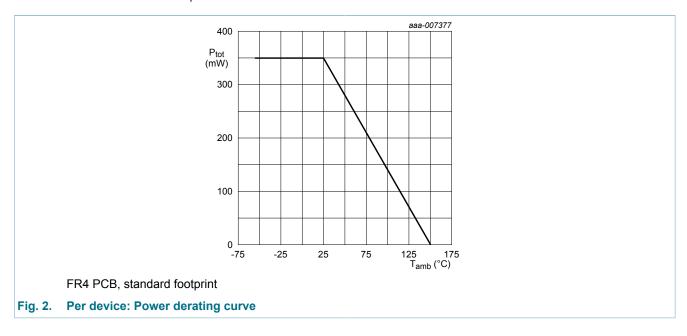
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor; for the PNP transistor with	negative polarity				
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
I <sub>BM</sub>	peak base current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	230	mW
Per device				'	'	,
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	350	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r						
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

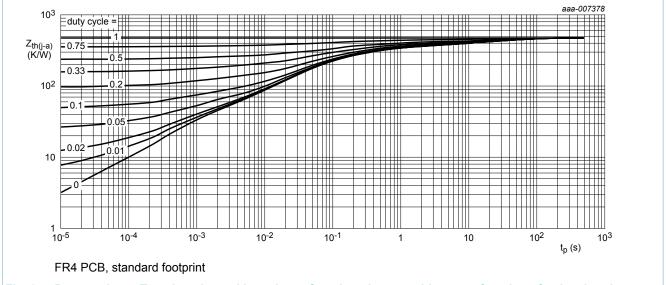


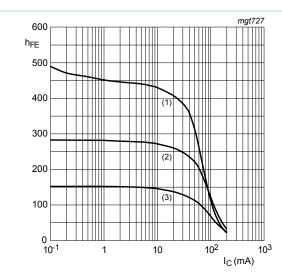
Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor; for the PNP transistor	with negative polarity				
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	15	nA
	current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C	200	-	450	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C	-	-	100	mV
saturation voltage		$I_{C}$ = 100 mA; $I_{B}$ = 5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	300	mV
V <sub>BEsat</sub> base-emitter saturation voltage		I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C	-	760	-	mV
	$I_C$ = 100 mA; $I_B$ = 5 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	900	-	mV	
V <sub>BE</sub> base-emitter voltage	$V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$	600	660	725	mV	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	710	820	mV
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	4	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
NF	noise figure	$V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ; f = 1 MHz; B = 200 Hz; $T_{amb}$ = 25 °C	-	-	10	dB
TR1 (NPN)						
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = 0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	11	-	pF
TR2 (PNP)			I			
C <sub>e</sub>	emitter capacitance	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	10	-	pF

### 45 V, 100 mA NPN/PNP general-purpose transistor



$$V_{CE} = 5 V$$

(1) 
$$T_{amb}$$
 = 150 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. NPN transistor: DC current gain as a function of collector current; typical values

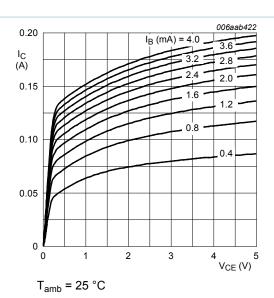
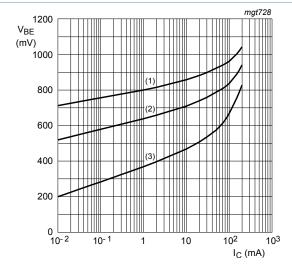


Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



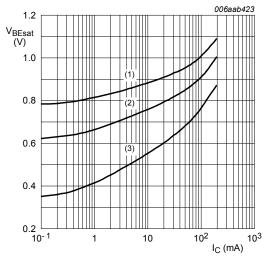
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 6. NPN transistor: Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

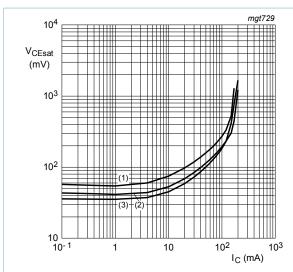
(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values

### 45 V, 100 mA NPN/PNP general-purpose transistor



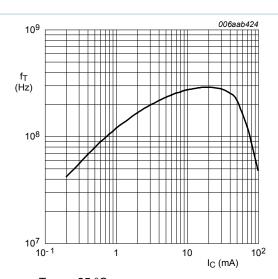
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

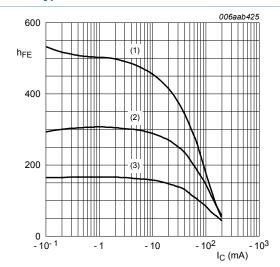
Fig. 8. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C;  
 $V_{CE}$  = 5 V;

f = 100 MHz

Fig. 9. Transition frequency as a function of collector current; typical values



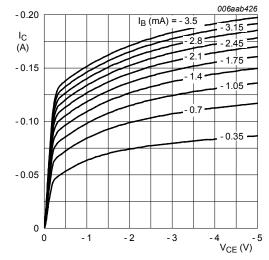


(1) 
$$T_{amb}$$
 = 150 °C

(2) 
$$T_{amb}$$
 = 25 °C

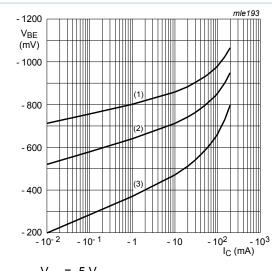
(3) 
$$T_{amb} = -55$$
 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



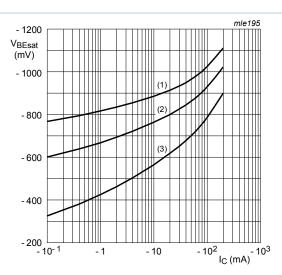
$$V_{CF} = -5 V$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 12. PNP transistor: Base-emitter voltage as a function of collector current; typical values



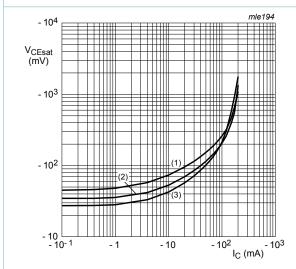
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



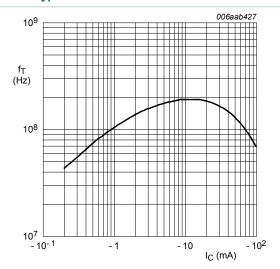
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C;$$

$$V_{CE} = -5 V;$$

f = 100 MHz

Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values

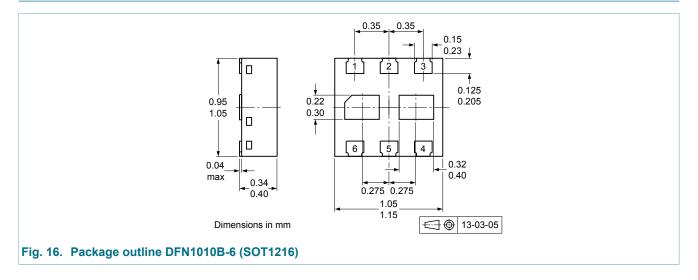
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## 11. Test information

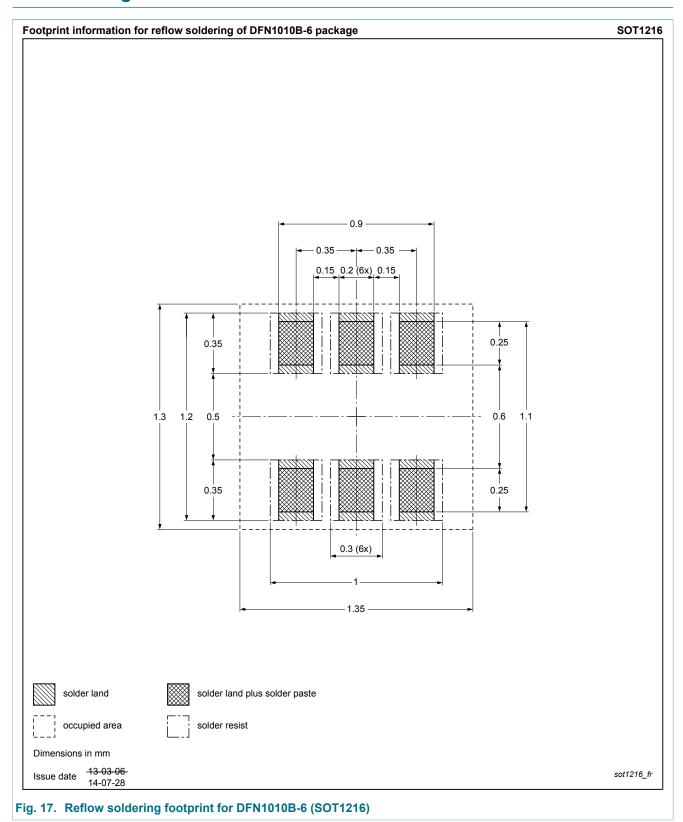
## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



## 13. Soldering



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45 V, 100 mA NPN/PNP general-purpose transistor

# 14. Revision history

### Table 8. Revision history

Data alcast ID	Dalama data	Data about status	01	0
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847QAPN v.2	20150708	Product data sheet	_	BC847QAPN v.1
Modification:	<ul> <li>Change of binary n</li> </ul>	narking code position.		
BC847QAPN v.1	20130718	Product data sheet		_
DO0-1 Q/ (1 1 V. 1	20100710	i roddol dala sricci		

# 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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